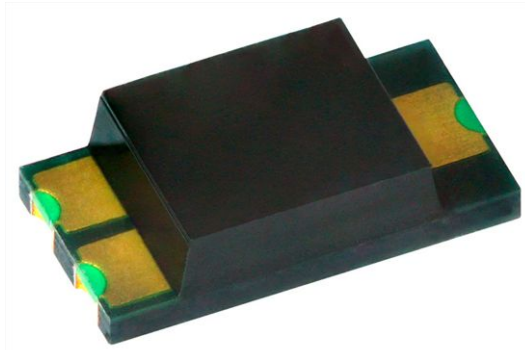


Silicon PIN Photodiode


 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE
GREEN
(5-2008)

FEATURES

- Package type: surface mount
- Package form: 1206
- Dimensions (L x W x H in mm): 4 x 2 x 1.05
- Radiant sensitive area (in mm²): 0.85
- High photo sensitivity
- High radiant sensitivity
- Daylight blocking filter matched with 830 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 60^\circ$
- Floor life: 72 h, MSL 4, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- High speed photo detector

DESCRIPTION

VEMD6110X01 is a high speed and high sensitive PIN photodiode. It is a small surface mount device (SMD) including the chip with a 0.85 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength of 830 nm to 950 nm.

PRODUCT SUMMARY

COMPONENT	I_{ra} (μ A)	ϕ (deg)	$\lambda_{0.5}$ (nm)
VEMD6110X01	9.5	± 60	750 to 1050

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VEMD6110X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	1206

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	32	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	215	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	-40 to +110	$^\circ\text{C}$
Storage temperature range		T_{stg}	-40 to +110	$^\circ\text{C}$
Soldering temperature	Acc. reflow solder profile fig. 8	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	Acc. J-STD-051	R_{thJA}	270	K/W

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	V_F		1		V
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$, $E = 0$	$V_{(BR)}$	32			V
Reverse dark current	$V_R = 10\text{ V}$, $E = 0$	I_{ro}		1	3	nA
Diode capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		12		pF
	$V_R = 5\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		3.6		pF
Open circuit voltage	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	V_o		356		mV
Temperature coefficient of V_o	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{V_o}		-3.1		mV/K
Short circuit current	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	I_k		9		μA
Temperature coefficient of I_k	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{I_k}		0.1		%/K
Reverse light current	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$, $V_R = 5\text{ V}$	I_{ra}	6.7	9.5	12.4	μA
Angle of half sensitivity		ϕ		± 60		deg
Wavelength of peak sensitivity		λ_p		950		nm
Range of spectral bandwidth		$\lambda_{0.5}$	750		1050	nm
Rise time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_r		100		ns
Fall time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_f		100		ns

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

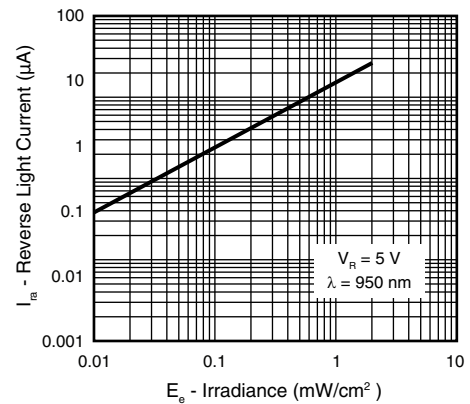


Fig. 3 - Reverse Light Current vs. Irradiance

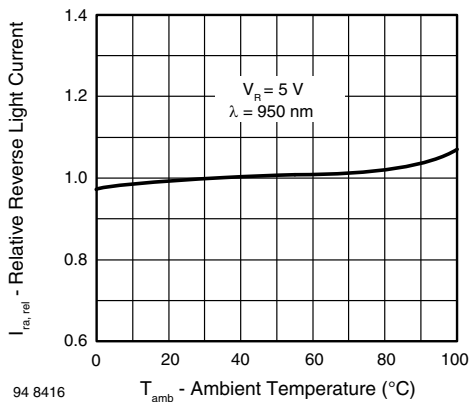


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

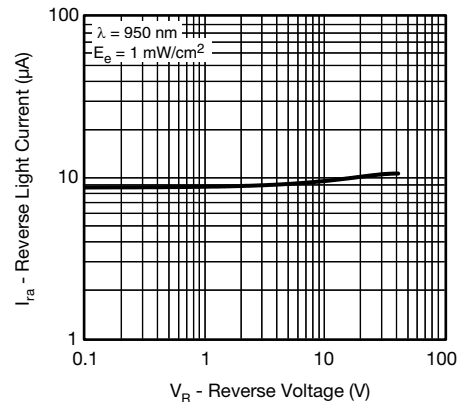


Fig. 4 - Reverse Light Current vs. Reverse Voltage

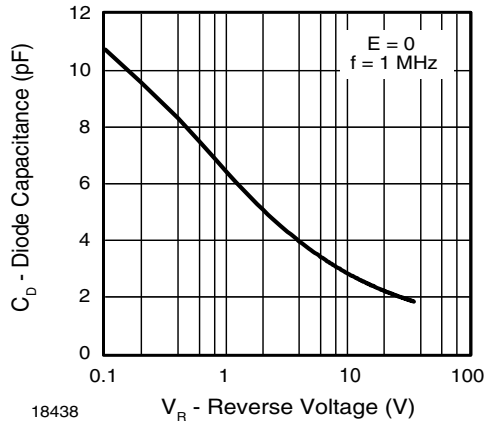


Fig. 5 - Diode Capacitance vs. Reverse Voltage

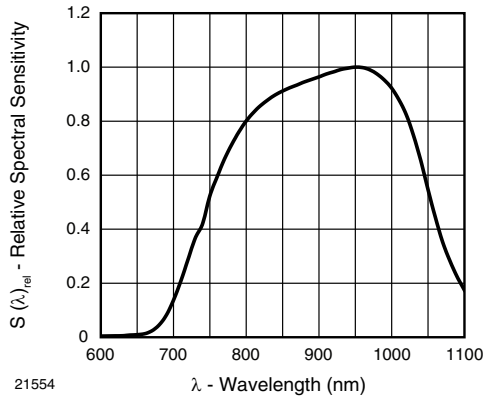


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

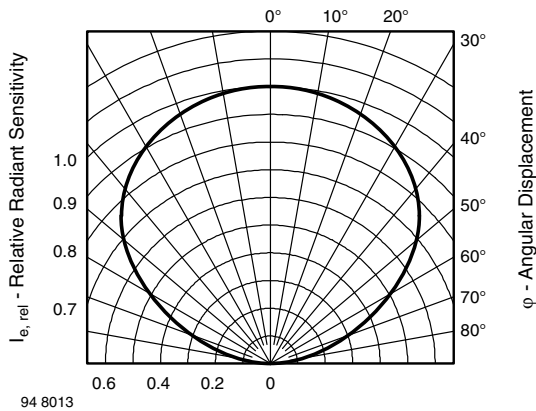


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

REFLOW SOLDER PROFILE

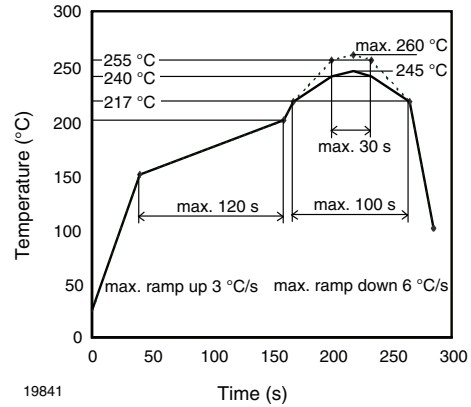


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 72 h

Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, $RH < 60\%$

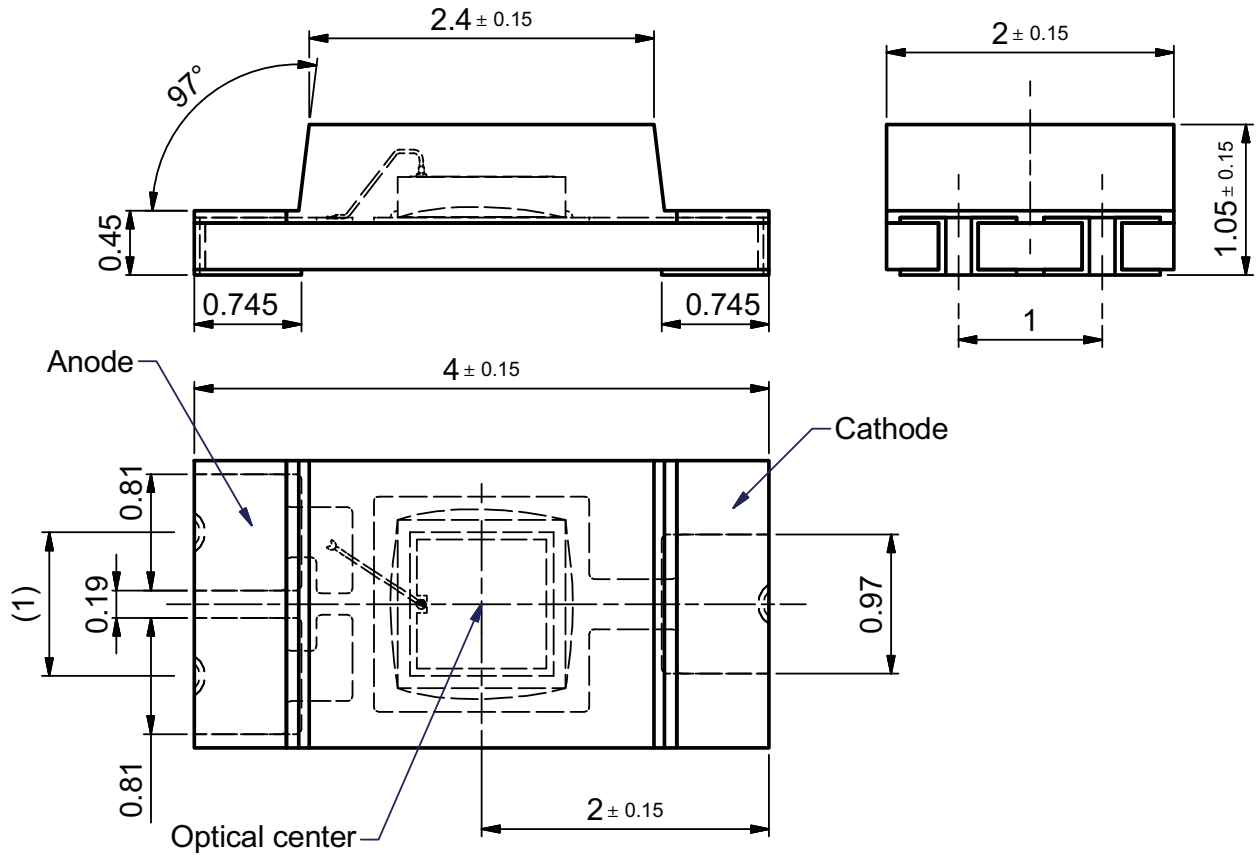
Moisture sensitivity level 4, acc. to J-STD-020.

DRYING

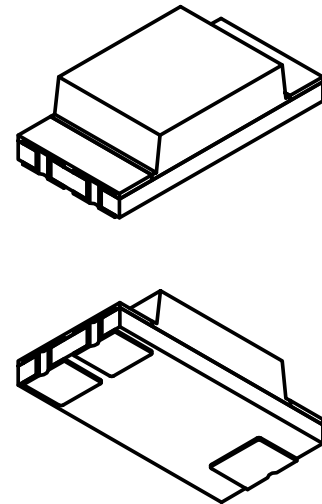
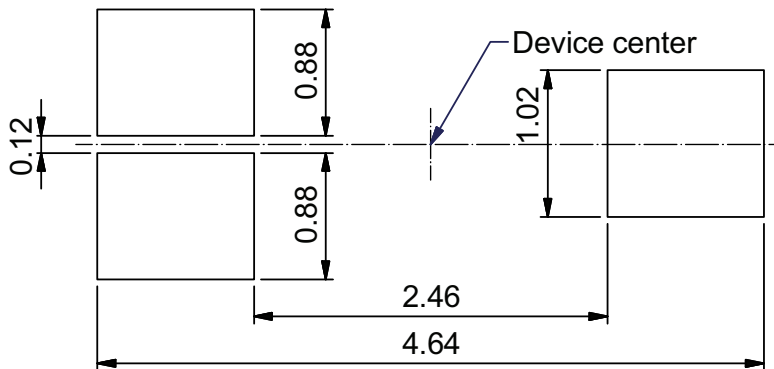
In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at $40\text{ }^{\circ}\text{C}$ (+ $5\text{ }^{\circ}\text{C}$), $RH < 5\%$.



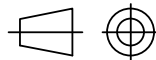
PACKAGE DIMENSIONS in millimeters



Recommended solder pad footprint



Drawing-No. 6.541-5100.01-4
Preliminary issue 04.07.2013

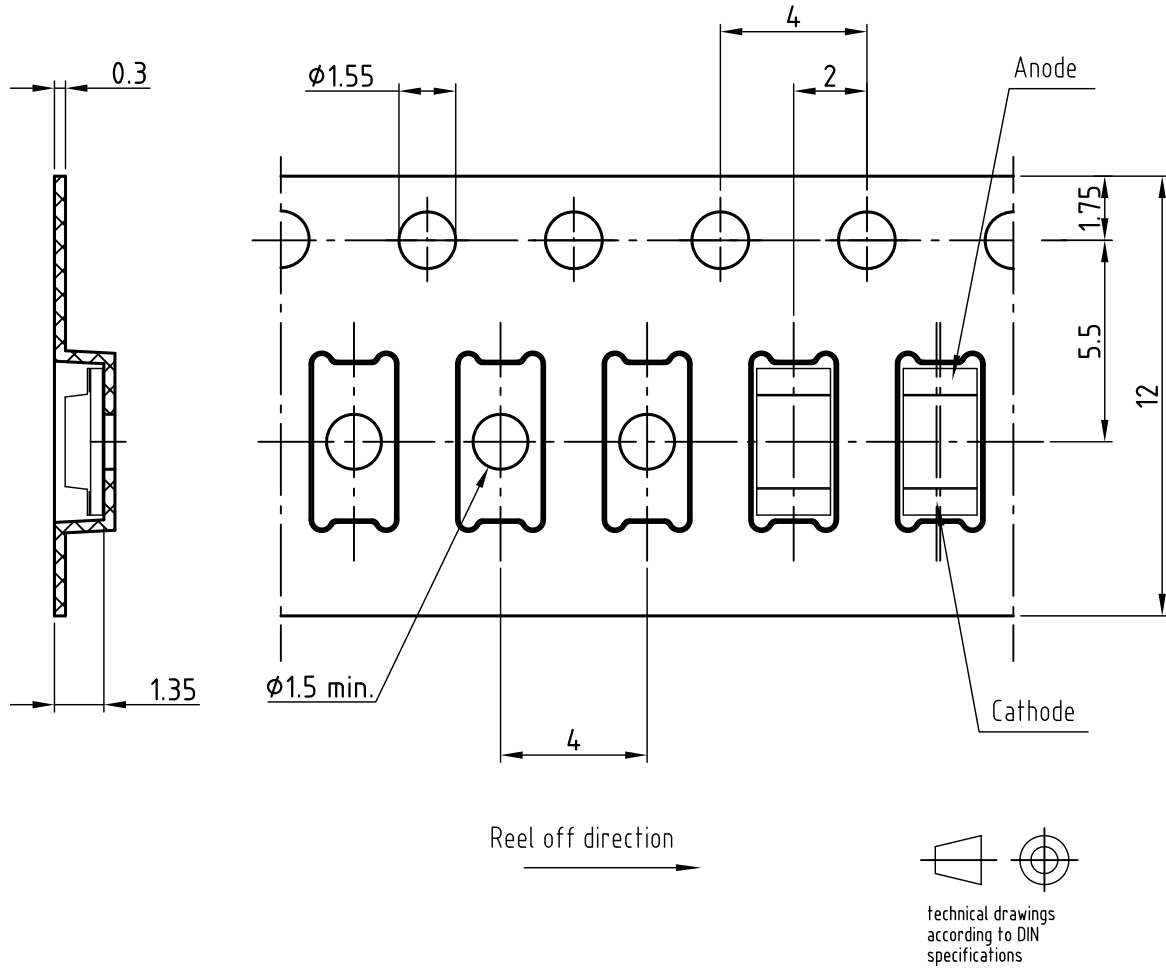


Technical drawings according to DIN specification.

Not indicated tolerances ± 0.1 mm



BLISTER TAPE DIMENSIONS in millimeters



Not indicated tolerances ±0.1

All dimensions in mm

Drawing refers to following Types: TEMD6010FX01

VEMD6x10X01

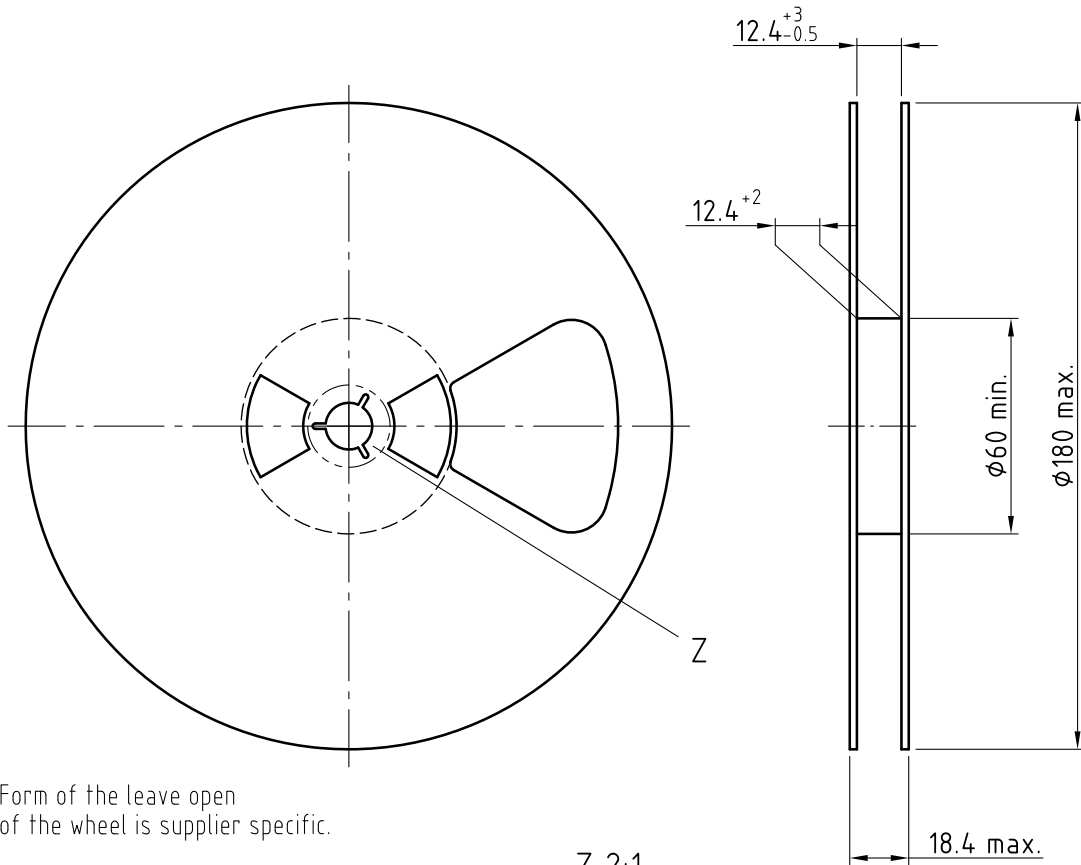
Drawing-No.: 9.700-5329.02-4

VEMD6x15X01

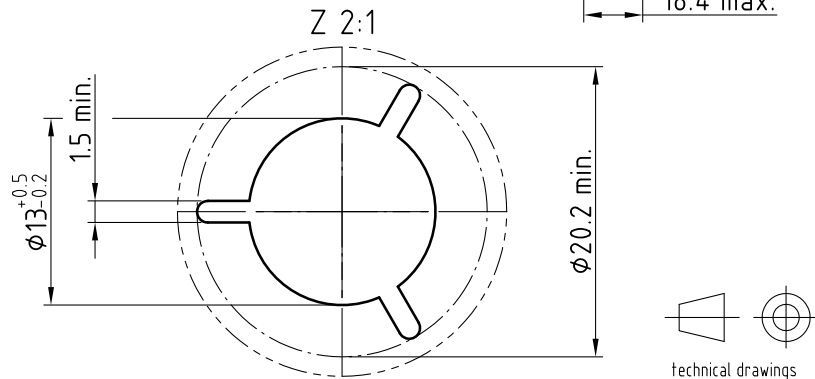
Prel Issue: 16.07.2013



REEL DIMENSIONS in millimeters



Form of the leave open of the wheel is supplier specific.



technical drawings according to DIN specifications

Drawing-No.: 9.800-5097.01-4

Issue: 1; 05.05.08

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